

AMENDMENTS TO THE CLAIMS

1. (Canceled).

2. (Canceled).

3. (Canceled).

4. (Currently Amended) ~~The~~ A semiconductor integrated circuit device as claimed in claim 3, comprising:

an output circuit,

wherein the output circuit comprises:

an open-drain N-channel MOSFET; and

an output terminal connected to a drain of the open-drain N-channel MOSFET,

wherein the open-drain N-channel MOSFET comprises:

a drain region formed of an N-type semiconductor layer;

a P-type impurity diffusion layer formed within the drain region;

two high-concentration N-type impurity diffusion layers formed within the drain region so as to sandwich the P-type impurity diffusion layer;

a low-concentration N-type impurity diffusion region formed in contact with the drain region; and

a drain electrode connected to the P-type impurity diffusion layer and to the two high-concentration N-type impurity diffusion layers,

wherein there are provided a plurality of the output circuit,

wherein a peripheral portion of the drain region of the open-drain N-channel MOSFET and a peripheral portion of a source region of the open-drain N-channel MOSFET each have, as seen in a plan view, a substantially circular shape or a substantially regular-polygonal shape with four or more sides, and gates of the open-drain N-channel MOSFET are formed in a net-like pattern,

5. (Currently Amended) ~~A~~ The semiconductor integrated circuit device as claimed in claim 3, comprising:

an output circuit,

wherein the output circuit comprises:

an open-drain N-channel MOSFET; and

an output terminal connected to a drain of the open-drain N-channel MOSFET,

wherein the open-drain N-channel MOSFET comprises:

a drain region formed of an N-type semiconductor layer;

a P-type impurity diffusion layer formed within the drain region;

two high-concentration N-type impurity diffusion layers formed within the drain region so as to sandwich the P-type impurity diffusion layer;

a low-concentration N-type impurity diffusion region formed in contact with the drain region; and

a drain electrode connected to the P-type impurity diffusion layer and to the two high-concentration N-type impurity diffusion layers,

wherein there are provided a plurality of the output circuit,

wherein the drain region and a source region of the open-drain N-channel MOSFET are formed in a pattern like teeth of a comb.

6. (Currently Amended) Δ The semiconductor integrated circuit device as claimed in claim 3, comprising:

an output circuit,

wherein the output circuit comprises:

an open-drain N-channel MOSFET; and

an output terminal connected to a drain of the open-drain N-channel MOSFET,

wherein the open-drain N-channel MOSFET comprises:

a drain region formed of an N-type semiconductor layer;

a P-type impurity diffusion layer formed within the drain region;

two high-concentration N-type impurity diffusion layers formed within the drain region so as to sandwich the P-type impurity diffusion layer;

a low-concentration N-type impurity diffusion region formed in contact with the drain region; and

a drain electrode connected to the P-type impurity diffusion layer and to the two high-concentration N-type impurity diffusion layers,

wherein there are provided a plurality of the output circuit,

wherein a peripheral portion of the drain region of the open-drain N-channel MOSFET and a peripheral portion of a source region of the open-drain N-channel MOSFET have, as seen in a plan view, different shapes.

7. (Currently Amended) The semiconductor integrated circuit device as claimed in claim 3 ~~4~~.

~~wherein a peripheral portion of the drain region of the open-drain N-channel MOSFET and a peripheral portion of a source region of the open-drain N-channel MOSFET each have, as seen in a plan view, a substantially circular shape or a substantially regular polygonal shape with four or more sides, and gates of the open-drain N-channel MOSFET are formed in a net-like pattern;~~

wherein the drain region and the source region of the open-drain N-channel MOSFET are formed in a pattern like teeth of a comb, and

wherein the peripheral portion of the drain region of the open-drain N-channel MOSFET and the peripheral portion of the source region of the open-drain N-channel MOSFET have, as seen in a plan view, different shapes.